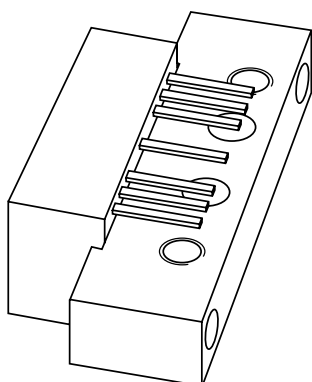


DATA SHEET



BGD502

550 MHz, 18.5 dB gain power
doubler amplifier

Product specification
Supersedes data of 1995 Oct 25

2001 Nov 15

550 MHz, 18.5 dB gain power doubler amplifier

BGD502

FEATURES

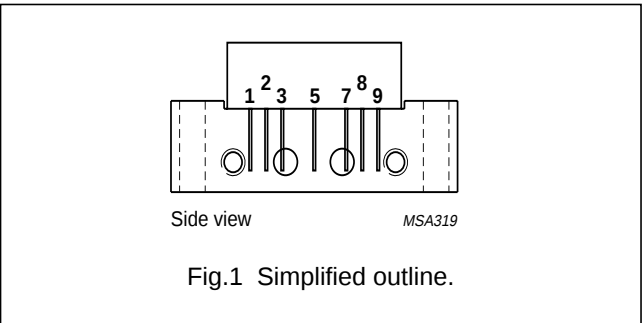
- Excellent linearity
- Extremely low noise
- Silicon nitride passivation
- Rugged construction
- TiPtAu metallized crystals ensure optimal reliability.

DESCRIPTION

Hybrid amplifier modules for CATV systems operating over a frequency range of 40 to 550 MHz at a voltage supply of 24 V (DC).

PINNING - SOT115J

PIN	DESCRIPTION
1	input
2, 3	common
5	+V _B
7, 8	common
9	output



QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
G _p	power gain	f = 50 MHz	18	19	dB
		f = 550 MHz	18.8	20.8	dB
I _{tot}	total current consumption (DC)	V _B = 24 V	—	435	mA

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	MIN.	MAX.	UNIT
V _i	RF input voltage	—	65	dBmV
T _{stg}	storage temperature	−40	+100	°C
T _{mb}	operating mounting base temperature	−20	+100	°C

550 MHz, 18.5 dB gain power doubler amplifier

BGD502

CHARACTERISTICS

Table 1 Bandwidth 40 to 550 MHz; $V_B = 24$ V; $T_{mb} = 35$ °C; $Z_S = Z_L = 75$ Ω.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
G_p	power gain	$f = 50$ MHz	18	–	19	dB
		$f = 550$ MHz	18.8	–	20.8	dB
SL	slope cable equivalent	$f = 40$ to 550 MHz	0.2	–	2.2	dB
FL	flatness of frequency response	$f = 40$ to 550 MHz	–	–	± 0.3	dB
S_{11}	input return losses	$f = 40$ to 80 MHz	20	–	–	dB
		$f = 80$ to 160 MHz	19	–	–	dB
		$f = 160$ to 550 MHz	18	–	–	dB
S_{22}	output return losses	$f = 40$ to 80 MHz	20	–	–	dB
		$f = 80$ to 160 MHz	19	–	–	dB
		$f = 160$ to 550 MHz	18	–	–	dB
S_{21}	phase response	$f = 50$ MHz	+135	–	+225	deg
CTB	composite triple beat	77 channels flat; $V_o = 44$ dBmV; measured at 547.25 MHz	–	–	–65	dB
X_{mod}	cross modulation	77 channels flat; $V_o = 44$ dBmV; measured at 55.25 MHz	–	–	–68	dB
CSO	composite second order distortion	77 channels flat; $V_o = 44$ dBmV; measured at 548.5 MHz	–	–	–62	dB
d_2	second order distortion	note 1	–	–	–72	dB
V_o	output voltage	$d_{im} = -60$ dB; note 2	64	–	–	dBmV
NF	noise figure	$f = 550$ MHz	–	–	8	dB
I_{tot}	total current consumption (DC)	note 3	–	415	435	mA

Notes

1. $f_p = 55.25$ MHz; $V_p = 44$ dBmV; $f_q = 493.25$ MHz; $V_q = 44$ dBmV; measured at $f_p + f_q = 548.5$ MHz.
2. Measured according to DIN45004B: $f_p = 540.25$ MHz; $V_p = V_o$; $f_q = 547.25$ MHz; $V_q = V_o - 6$ dB;
 $f_r = 549.25$ MHz; $V_r = V_o - 6$ dB; measured at $f_p + f_q - f_r = 538.25$ MHz.
3. The module normally operates at $V_B = 24$ V, but are able to withstand supply transients up to $V_B = 30$ V.

550 MHz, 18.5 dB gain power doubler amplifier

BGD502

Table 2 Bandwidth 40 to 450 MHz; $V_B = 24$ V; $T_{mb} = 35$ °C; $Z_S = Z_L = 75$ Ω .

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
G_p	power gain	$f = 50$ MHz	18	–	19	dB
		$f = 450$ MHz	18.6	–	20.6	dB
SL	slope cable equivalent	$f = 40$ to 450 MHz	0.2	–	1.8	dB
FL	flatness of frequency response	$f = 40$ to 450 MHz	–	–	± 0.3	dB
S_{11}	input return losses	$f = 40$ to 80 MHz	20	–	–	dB
		$f = 80$ to 160 MHz	19	–	–	dB
		$f = 160$ to 450 MHz	18	–	–	dB
S_{22}	output return losses	$f = 40$ to 80 MHz	20	–	–	dB
		$f = 80$ to 160 MHz	19	–	–	dB
		$f = 160$ to 450 MHz	18	–	–	dB
S_{21}	phase response	$f = 50$ MHz	+135	–	+225	deg
CTB	composite triple beat	60 channels flat; $V_o = 46$ dBmV; measured at 445.25 MHz	–	–	–67	dB
CSO	composite second order distortion	60 channels flat; $V_o = 46$ dBmV; measured at 446.5 MHz	–	–	–60	dB
X_{mod}	cross modulation	60 channels flat; $V_o = 46$ dBmV; measured at 55.25 MHz	–	–	–67	dB
d_2	second order distortion	note 1	–	–	–75	dB
V_o	output voltage	$d_{im} = -60$ dB; note 2	67	–	–	dBmV
NF	noise figure	$f = 450$ MHz	–	–	7	dB
I_{tot}	total current consumption (DC)	note 3	–	415	435	mA

Notes

1. $f_p = 55.25$ MHz; $V_p = 46$ dBmV; $f_q = 391.25$ MHz; $V_q = 46$ dBmV; measured at $f_p + f_q = 446.5$ MHz.
2. Measured according to DIN45004B: $f_p = 440.25$ MHz; $V_p = V_o$; $f_q = 447.25$ MHz; $V_q = V_o - 6$ dB;
 $f_r = 449.25$ MHz; $V_r = V_o - 6$ dB; measured at $f_p + f_q - f_r = 438.25$ MHz.
3. The modules normally operate at $V_B = 24$ V, but are able to withstand supply transients up to $V_B = 30$ V.

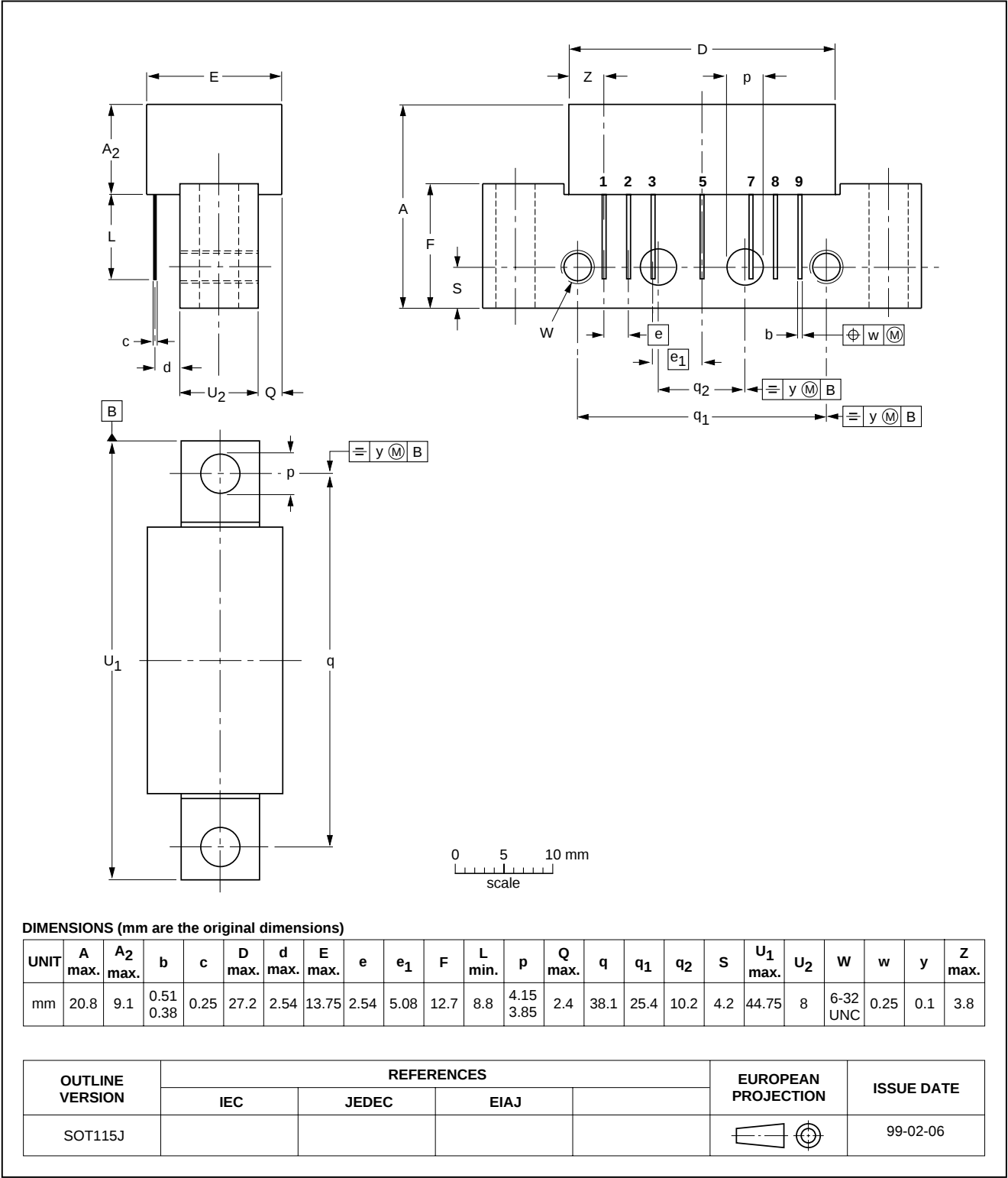
550 MHz, 18.5 dB gain power doubler amplifier

BGD502

PACKAGE OUTLINE

Rectangular single-ended package; aluminium flange; 2 vertical mounting holes;
2 x 6-32 UNC and 2 extra horizontal mounting holes; 7 gold-plated in-line leads

SOT115J



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BGD502

DATA SHEET STATUS

DATA SHEET STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITIONS
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This product is supplied in anti-static packing to prevent damage caused by electrostatic discharge during transport and handling. For further information, refer to Philips specs.: SNW-EQ-608, SNW-FQ-302A and SNW-FQ-302B.

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BGD502

NOTES

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